Frederic Wrobel

List of Publications by Year in descending order

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623734 580821 35 640 14 25 citations g-index h-index papers 35 35 35 491 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Anthology of the Development of Radiation Transport Tools as Applied to Single Event Effects. IEEE Transactions on Nuclear Science, 2013, 60, 1876-1911.	2.0	119
2	Criterion for SEU occurrence in SRAM deduced from circuit and device Simulations in case of neutron-induced SER. IEEE Transactions on Nuclear Science, 2005, 52, 1148-1155.	2.0	63
3	Multiple Cell Upset Classification <newline></newline> in Commercial SRAMs. IEEE Transactions on Nuclear Science, 2014, 61, 1747-1754.	2.0	46
4	MC-ORACLE: A tool for predicting Soft Error Rate. Computer Physics Communications, 2011, 182, 317-321.	7.5	45
5	Determining Realistic Parameters for the <newline></newline> Double Exponential Law that Models <newline></newline> Transient Current Pulses. IEEE Transactions on Nuclear Science, 2014, 61, 1813-1818.	2.0	36
6	SEL Hardness Assurance in a Mixed Radiation Field. IEEE Transactions on Nuclear Science, 2015, 62, 2555-2562.	2.0	30
7	Dynamic Test Methods for COTS SRAMs. IEEE Transactions on Nuclear Science, 2014, 61, 3095-3102.	2.0	26
8	Energy Dependence of Tungsten-Dominated SEL Cross Sections. IEEE Transactions on Nuclear Science, 2014, 61, 2718-2726.	2.0	25
9	SEL Cross Section Energy Dependence Impact on the High Energy Accelerator Failure Rate. IEEE Transactions on Nuclear Science, 2014, 61, 2936-2944.	2.0	22
10	Floating Gate Dosimeter Suitability for Accelerator-like Environments. IEEE Transactions on Nuclear Science, 2017, , 1-1.	2.0	21
11	Detailed history of recoiling ions induced by nucleons. Computer Physics Communications, 2008, 178, 88-104.	7. 5	19
12	0.1–10 MeV Neutron Soft Error Rate in Accelerator and Atmospheric Environments. IEEE Transactions on Nuclear Science, 2021, 68, 873-883.	2.0	18
13	Impact of Electrical Stress and Neutron Irradiation on Reliability of Silicon Carbide Power MOSFET. IEEE Transactions on Nuclear Science, 2020, 67, 1365-1373.	2.0	16
14	Thermal Neutron-Induced SEUs in the LHC Accelerator Environment. IEEE Transactions on Nuclear Science, 2020, 67, 1412-1420.	2.0	14
15	Single-Event Effects in the Peripheral Circuitry of a Commercial Ferroelectric Random Access Memory. IEEE Transactions on Nuclear Science, 2018, 65, 1708-1714.	2.0	12
16	Analysis of the charge sharing effect in the SET sensitivity of bulk 45â€nm standard cell layouts under heavy ions. Microelectronics Reliability, 2018, 88-90, 920-924.	1.7	12
17	SEE Flux and Spectral Hardness Calibration of Neutron Spallation and Mixed-Field Facilities. IEEE Transactions on Nuclear Science, 2019, 66, 1532-1540.	2.0	12
18	Direct Ionization Impact on Accelerator Mixed-Field Soft-Error Rate. IEEE Transactions on Nuclear Science, 2020, 67, 345-352.	2.0	12

#	Article	IF	Citations
19	Neutron-Induced Failure Dependence on Reverse Gate Voltage for SiC Power MOSFETs in Atmospheric Environment. IEEE Transactions on Nuclear Science, 2021, 68, 1623-1632.	2.0	11
20	Investigation on Passive and Autonomous Mode Operation of Floating Gate Dosimeters. IEEE Transactions on Nuclear Science, 2019, 66, 1620-1627.	2.0	10
21	Radiation hardening efficiency of gate sizing and transistor stacking based on standard cells. Microelectronics Reliability, 2019, 100-101, 113457.	1.7	8
22	A Simple Method for Assessing Power Devices Sensitivity to SEEs in Atmospheric Environment. IEEE Transactions on Nuclear Science, 2013, 60, 2559-2566.	2.0	7
23	Impact of Complex Logic Cell Layout on the Single-Event Transient Sensitivity. IEEE Transactions on Nuclear Science, 2019, 66, 1465-1472.	2.0	7
24	Analysis of SET Propagation in a System in Package Point of Load Converter. IEEE Transactions on Nuclear Science, 2020, 67, 1494-1502.	2.0	7
25	Post-Irradiation-Gate-Stress on Power MOSFETs: Quantification of Latent Defects-Induced Reliability Degradation. IEEE Transactions on Nuclear Science, 2013, 60, 4166-4174.	2.0	6
26	Gate Voltage Contribution to Neutron-Induced SEB of Trench Gate Fieldstop IGBT. IEEE Transactions on Nuclear Science, 2014, 61, 1739-1746.	2.0	6
27	Design exploration of majority voter architectures based on the signal probability for TMR strategy optimization in space applications. Microelectronics Reliability, 2020, 114, 113877.	1.7	5
28	Mitigation and Predictive Assessment of SET Immunity of Digital Logic Circuits for Space Missions. Aerospace, 2020, 7, 12.	2.2	5
29	Analysis of Single-Event Effects in DDR3 and DDR3L SDRAMs Using Laser Testing and Monte-Carlo Simulations. IEEE Transactions on Nuclear Science, 2018, 65, 262-268.	2.0	4
30	Impact of Energy Dependence on Ground Level and Avionic SEE Rate Prediction When Applying Standard Test Procedures. Aerospace, 2019, 6, 119.	2.2	4
31	Exploiting Transistor Folding Layout as RHBD Technique Against Single-Event Transients. IEEE Transactions on Nuclear Science, 2020, 67, 1581-1589.	2.0	4
32	Impact of Atmospheric and Space Radiation on Sensitive Electronic Devices. , 2022, , .		4
33	The Power Law Shape of Heavy Ions Experimental Cross Section. IEEE Transactions on Nuclear Science, 2017, 64, 427-433.	2.0	3
34	Investigation on the Sensitivity Degradation of Dosimeters based on Floating Gate Structure. , 2017, , .		1
35	Reliability-driven pin assignment optimization to improve in-orbit soft-error rate. Microelectronics Reliability, 2020, 114, 113885.	1.7	0